

Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±10	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	240 190	mA
Continuous Drain Current (Note 6) V _{GS} = 1.8V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	180 140	mA
Pulsed Drain Current - T _P = 10μs			I_{DM}	805	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	409	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-55 to +150	°C

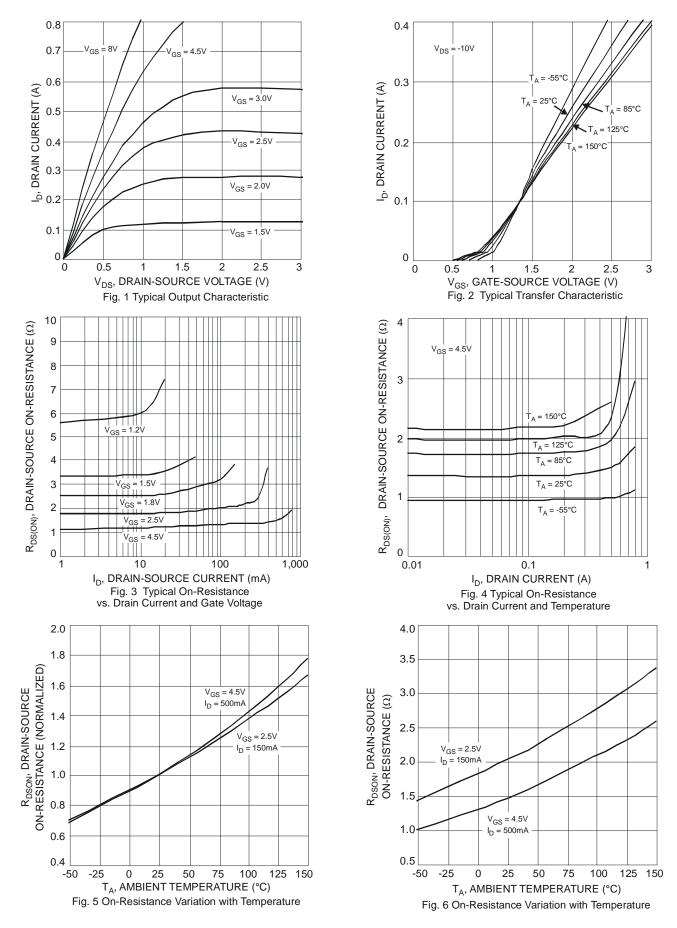
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20			٧	$V_{GS} = 0V, I_D = 100\mu A$	
Zero Gate Voltage Drain Current @ T _J = +25°C	1			500	nA	$V_{DS} = 20V, V_{GS} = 0V$	
@T _J = +85°C (Note 8)	I _{DSS}			1.7	μΑ	$V_{DS} = 2.6V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}		_	±1	μΑ	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
одие-войу Leakage			_	±100	nA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.45	0.8	1.05	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
			1.8	3.0	Ω	$V_{GS} = 4.5V, I_D = 100mA$	
	R _{DS} (ON)		2.5	4.0		$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance			3.4	6.0		$V_{GS} = 1.8V, I_D = 20mA$	
			4.7	10.0		$V_{GS} = 1.5V, I_D = 10mA$	
			9.5	_		$V_{GS} = 1.2V, I_D = 1mA$	
Forward Transconductance	Y _{fs}	180	240	_	mS	$V_{DS} = 10V, I_{D} = 0.1A$	
Source-Drain Diode Forward Voltage	V _{SD}	0.5	0.8	1.0	V	$V_{GS} = 0V, I_{S} = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		14.1	_	pF		
Output Capacitance	Coss		2.9	_	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	1.6	_	pF		
SWITCHING CHARACTERISTICS, V _{GS} = 4.5V (Note 8)							
Turn-On Delay Time	t _{d(on)}	_	3.8	_			
Rise Time	t _r	_	7.9	_	ns	$V_{GS} = 4.5V, V_{DD} = 10V$	
Turn-Off Delay Time	t _{d(off)}	_	13.4	_	$I_D = 200 \text{mA}, R_G = 2.0$		
Fall Time	t _f	_	15.2	_			

Notes:

- 6. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch with minimum recommended pad layout; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design, not subject to production testing.







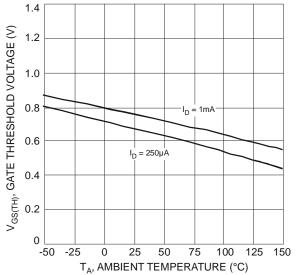
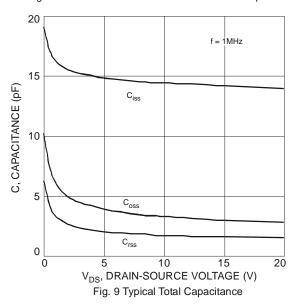
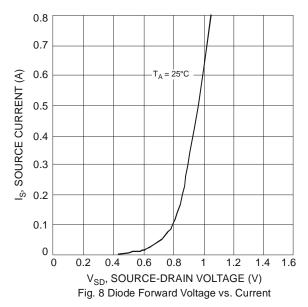


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





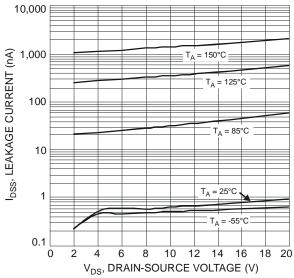
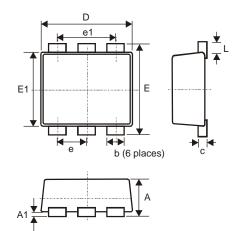


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



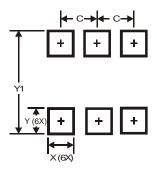
A 0.40 0.50 0.45 A1 0 0.05 - c 0.120 0.180 0.15 D 0.95 1.05 1.06 E 0.95 1.05 1.06 E1 0.75 0.85 0.80 L 0.05 0.15 0.10 b 0.10 0.20 0.18	501963					
A1 0 0.05 - c 0.120 0.180 0.15 D 0.95 1.05 1.06 E 0.95 1.05 1.05 E1 0.75 0.85 0.80 L 0.05 0.15 0.10 b 0.10 0.20 0.18	Dim	Min	Max	Тур		
c 0.120 0.180 0.15 D 0.95 1.05 1.06 E 0.95 1.05 1.05 E1 0.75 0.85 0.80 L 0.05 0.15 0.10 b 0.10 0.20 0.18	Α	0.40	0.50	0.45		
D 0.95 1.05 1.00 E 0.95 1.05 1.00 E1 0.75 0.85 0.80 L 0.05 0.15 0.10 b 0.10 0.20 0.15	A 1	0	0.05	-		
E 0.95 1.05 1.00 E1 0.75 0.85 0.80 L 0.05 0.15 0.10 b 0.10 0.20 0.15	С	0.120	0.180	0.150		
E1 0.75 0.85 0.80 L 0.05 0.15 0.10 b 0.10 0.20 0.15	D	0.95	1.05	1.00		
L 0.05 0.15 0.10 b 0.10 0.20 0.15	Е	0.95	1.05	1.00		
b 0.10 0.20 0.15	E1	0.75	0.85	0.80		
	L	0.05	0.15	0.10		
0.05 Tum	b	0.10	0.20	0.15		
e 0.35 Typ						
e1 0.70 Typ	e1	0.70 Typ				
All Dimensions in mm						

COTOGS



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.350
Х	0.200
Υ	0.200
Y1	1.100

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